



# SANYO SEMICONDUCTOR

## 2SD621

2SD621 NPN Triple Diffused Mesa Type Silicon Transistor  
For H-Deflection Output with High Voltage

### Absolute Maximum Ratings at Ta=25°C

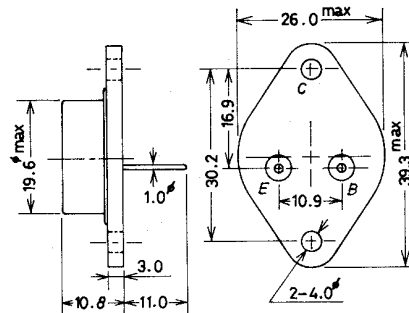
Collector to Base Voltage	V <sub>CB0</sub>	2500 V
Collector to Emitter Voltage	V <sub>CE0</sub>	900 V
Emitter to Base Voltage	V <sub>EB0</sub>	6 V
Collector Current	I <sub>C</sub>	3 A
Peak Collector Current	i <sub>cp</sub>	7 A
Collector Dissipation	P <sub>C</sub>	50 W
Junction Temperature	T <sub>j</sub>	150 °C
Storage Temperature	T <sub>stg</sub>	-40 to +150 °C

T<sub>c</sub>=25°C

### Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub> (1) V <sub>CB</sub> =1000V, I <sub>E</sub> =0			50	uA
	I <sub>CB0</sub> (2) V <sub>CB</sub> =2500V, I <sub>E</sub> =0			1.0	mA
Emitter Cutoff Current	I <sub>EB0</sub> V <sub>EB</sub> =6V, I <sub>C</sub> =0			1.0	mA
Collector Cutoff Current	I <sub>CE0</sub> V <sub>CE</sub> =900V, I <sub>B</sub> =0			10	mA
DC Current Gain	h <sub>FE</sub> V <sub>CE</sub> =10V, I <sub>C</sub> =1.5A	3		15	
C-E Saturation Voltage	V <sub>CE</sub> (sat) I <sub>C</sub> =1.5A, I <sub>B</sub> =0.5A			10	V
B-E Saturation Voltage	V <sub>BE</sub> (sat) I <sub>C</sub> =1.5A, I <sub>B</sub> =0.5A			1.25	V
Fall Time	t <sub>f</sub> i <sub>cp</sub> =1.5A			1.0	us

### Case Outline (unit:mm)



EIAJ. TC-3, TB-3  
JEDEC. TO-3

C. Collector  
E. Emitter  
B. Base